



STD11NM60N-1 - STB11NM60N-1 STD11NM60N-STP11NM60N-STF11NM60N

N-channel 600V - 0.37Ω - 10A - TO-220/FP- I/I²PAK - DPAK
second generation MDmesh™ Power MOSFET

Features

Type	V _{DSS} (@T _{Jmax})	R _{DS(on)}	I _D
STB11NM60N-1	650 V	< 0.45 Ω	10 A
STD11NM60N	650 V	< 0.45 Ω	10 A
STD11NM60N-1	650 V	< 0.45 Ω	10 A
STF11NM60N	650 V	< 0.45 Ω	10 A ⁽¹⁾
STP11NM60N	650 V	< 0.45 Ω	10 A

1. Limited only by maximum temperature allowed

- 100% avalanche tested
- Low input capacitance and gate charge
- Low gate input resistance

Application

- Switching applications

Description

This series of devices is designed using the second generation of MDmesh™ Technology. This revolutionary Power MOSFET associates a new vertical structure to the Company's strip layout to yield one of the world's lowest on-resistance and gate charge. It is therefore suitable for the most demanding high efficiency converters.

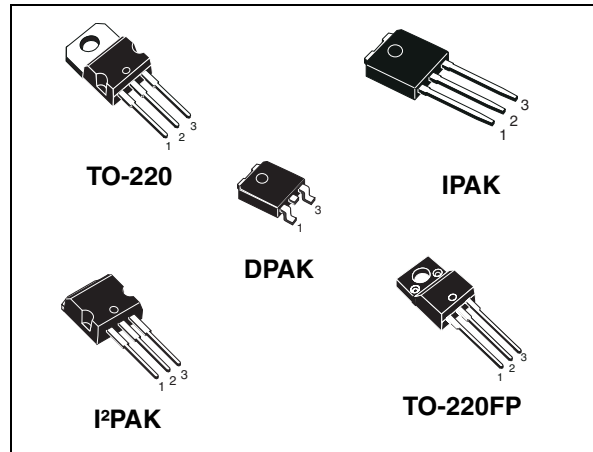


Figure 1. Internal schematic diagram

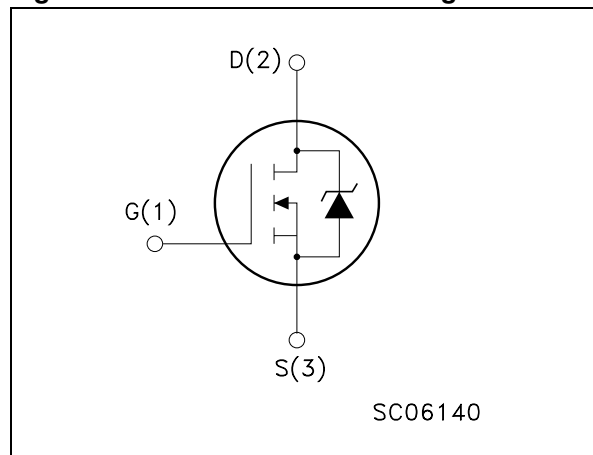


Table 1. Device summary

Order codes	Marking	Package	Packaging
STB11NM60N-1	B11NM60N	I ² PAK	Tube
STD11NM60N-1	D11NM60N	IPAK	Tube
STD11NM60N	D11NM60N	DPAK	Tape & reel
STP11NM60N	P11NM60N	TO-220	Tube
STF11NM60N	F11NM60N	TO-220FP	Tube

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value		Unit
		TO-220/I ² PAK DPAK/IPAK	TO-220FP	
V _{DS}	Drain-source voltage (V _{GS} = 0)	600		V
V _{GS}	Gate-source voltage	± 25		V
I _D	Drain current (continuous) at T _C = 25 °C	10	10 ⁽¹⁾	A
I _D	Drain current (continuous) at T _C = 100 °C	6.3	6.3 ⁽¹⁾	A
I _{DM} ⁽²⁾	Drain current (pulsed)	40	40 ⁽¹⁾	A
P _{TOT}	Total dissipation at T _C = 25 °C	90	25	W
	Derating factor	0.8	0.2	W/°C
dv/dt ⁽³⁾	Peak diode recovery voltage slope	15		V/ns
V _{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink (t = 1 s; T _C = 25 °C)	--	2500	V
T _J T _{stg}	Operating junction temperature Storage temperature	-55 to 150		°C

1. Limited only by maximum temperature allowed
2. Pulse width limited by safe operating area
3. I_{SD} ≤ 10A, di/dt ≤ 400A/μs, V_{DD} = 80% V_{(BR)DSS}

Table 3. Thermal data

Symbol	Parameter	Value		Unit
		TO-220 / I ² PAK DPAK / IPAK	TO-220FP	
R _{thj-case}	Thermal resistance junction-case max	1.38	5	°C/W
R _{thj-amb}	Thermal resistance junction-amb max	62.5		°C/W
T _l	Maximum lead temperature for soldering purposes	300		°C

Table 4. Avalanche characteristics

Symbol	Parameter	Max value	Unit
I _{AS}	Avalanche current, repetitive or not-repetitive (pulse width limited by T _J max)	3.5	A
E _{AS}	Single pulse avalanche energy (starting T _J = 25 °C, I _D = I _{AS} , V _{DD} = 50 V)	200	mJ

2 Electrical characteristics

($T_{CASE}=25^{\circ}C$ unless otherwise specified)

Table 5. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1 \text{ mA}, V_{GS} = 0$	600			V
$dv/dt^{(1)}$	Drain-source voltage slope	$V_{DD} = 400 \text{ V}, I_D = 5 \text{ A}, V_{GS} = 10 \text{ V}$		45		V/ns
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = \text{Max rating}, V_{DS} = \text{Max rating}, T_c = 125^{\circ}C$			1 10	μA μA
I_{GSS}	Gate body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20 \text{ V}$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$	2	3	4	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10 \text{ V}, I_D = 5 \text{ A}$		0.37	0.45	Ω

1. Characteristic value at turn off on inductive load

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$g_{fs}^{(1)}$	Forward transconductance	$V_{DS} = 15 \text{ V}, I_D = 5 \text{ A}$		7.5		S
C_{iss} C_{oss} C_{rss}	Input capacitance Output capacitance Reverse transfer capacitance	$V_{DS} = 50 \text{ V}, f = 1 \text{ MHz}, V_{GS} = 0$		850 44 5		pF pF pF
$C_{oss \text{ eq.}}^{(2)}$	Equivalent output capacitance	$V_{GS} = 0, V_{DS} = 0 \text{ V to } 480 \text{ V}$		130		pF
Rg	Gate input resistance	f=1 MHz Gate DC Bias=0 Test signal level=20 mV open drain		3.7		Ω
Q_g Q_{gs} Q_{gd}	Total gate charge Gate-source charge Gate-drain charge	$V_{DD} = 480 \text{ V}, I_D = 10 \text{ A}$ $V_{GS} = 10 \text{ V}$ (see Figure 19)		31 4.2 15.9		nC nC nC

1. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2. $C_{oss \text{ eq.}}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 7. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 300\text{ V}$, $I_D = 5\text{ A}$,		22		ns
t_r	Rise time	$R_G = 4.7\ \Omega$, $V_{GS} = 10\text{ V}$		18.5		ns
$t_{d(off)}$	Turn-off delay time	(see Figure 18)		50		ns
t_f	Fall time	(see Figure 23)		12		ns

Table 8. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current				10	A
I_{SDM}	Source-drain current (pulsed)				40	A
$V_{SD}^{(1)}$	Forward on voltage	$I_{SD} = 10\text{ A}$, $V_{GS}=0$			1.3	V
t_{rr}	Reverse recovery time	$I_{SD} = 10\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$,		340		ns
Q_{rr}	Reverse recovery charge	$V_{DD} = 100\text{ V}$, $T_J = 25\text{ }^\circ\text{C}$		3.26		μC
I_{RRM}	Reverse recovery current	(see Figure 20)		19.2		A
t_{rr}	Reverse recovery time	$V_{DD} = 100\text{ V}$		460		ns
Q_{rr}	Reverse recovery charge	$di/dt = 100\text{ A}/\mu\text{s}$, $I_{SD} = 10\text{ A}$		4.42		μC
I_{RRM}	Reverse recovery current	$T_J = 150\text{ }^\circ\text{C}$ (see Figure 20)		19.2		A

1. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for TO-220 / I²PAK

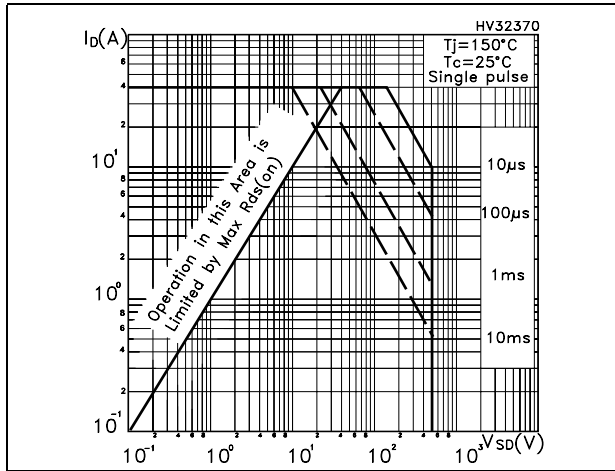


Figure 3. Thermal impedance for TO-220 / I²PAK

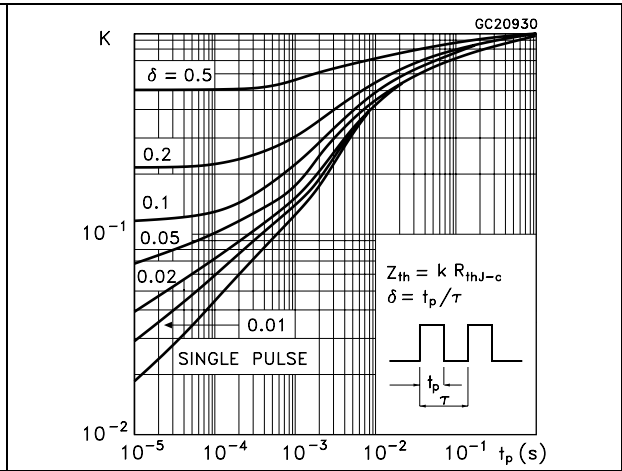


Figure 4. Safe operating area for TO-220FP

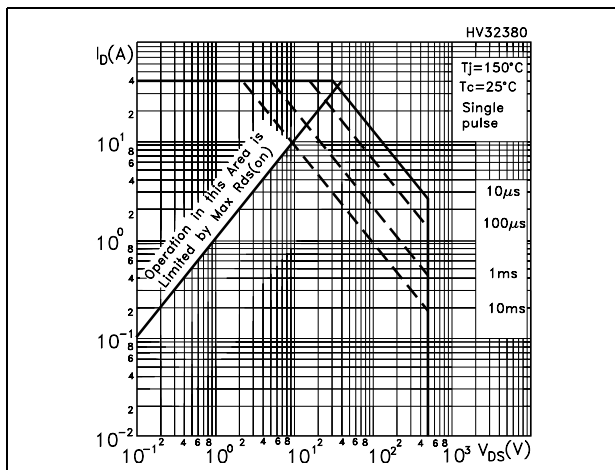


Figure 5. Thermal impedance for TO-220FP

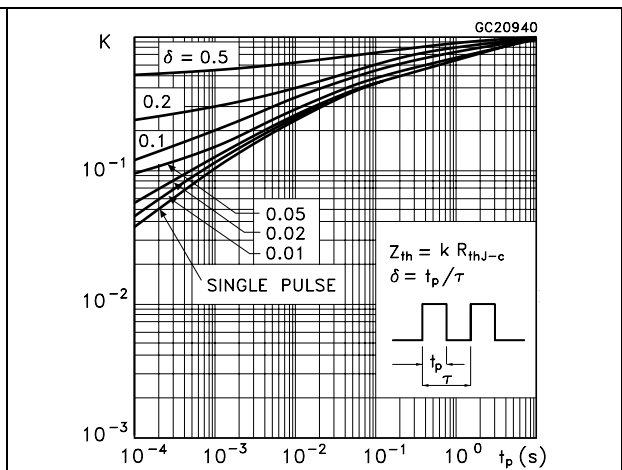


Figure 6. Safe operating area for DPAK / IPAK

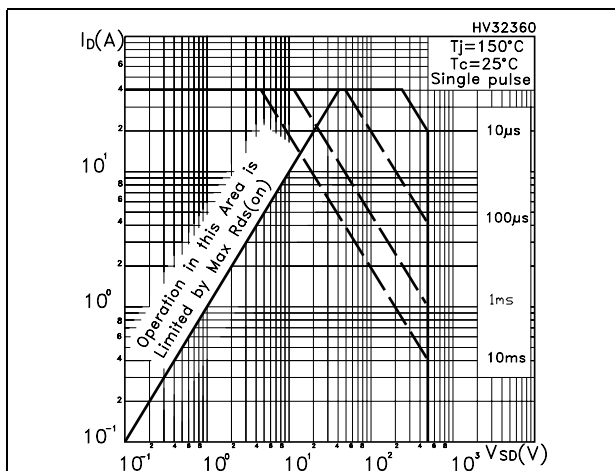


Figure 7. Thermal impedance for DPAK / IPAK

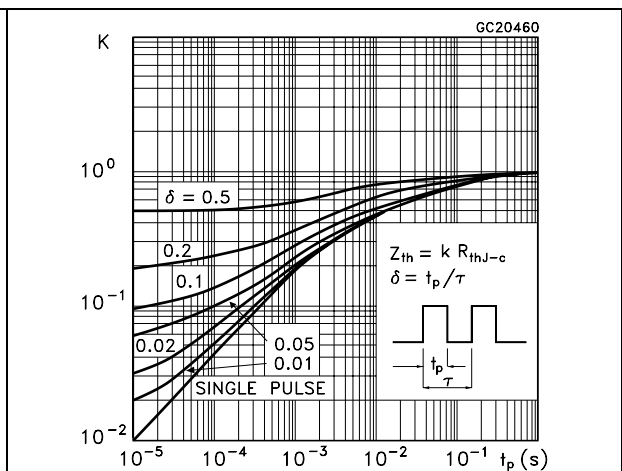


Figure 8. Output characteristics

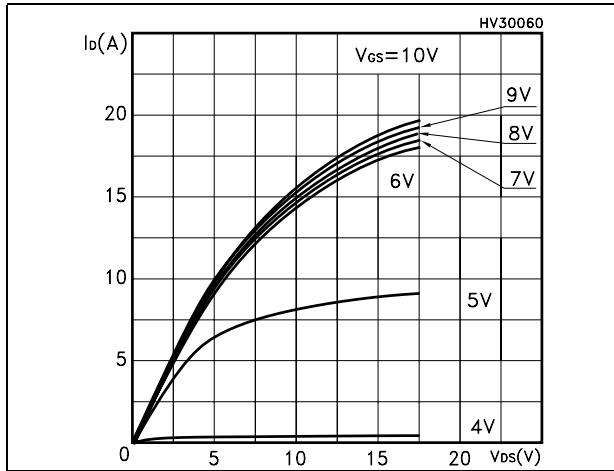


Figure 9. Transfer characteristics

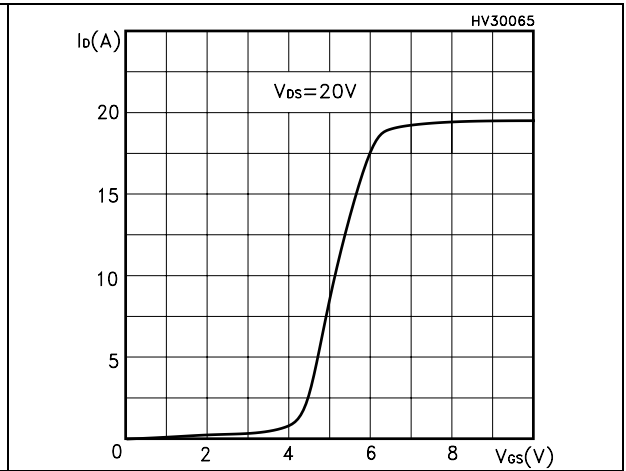


Figure 10. Transconductance

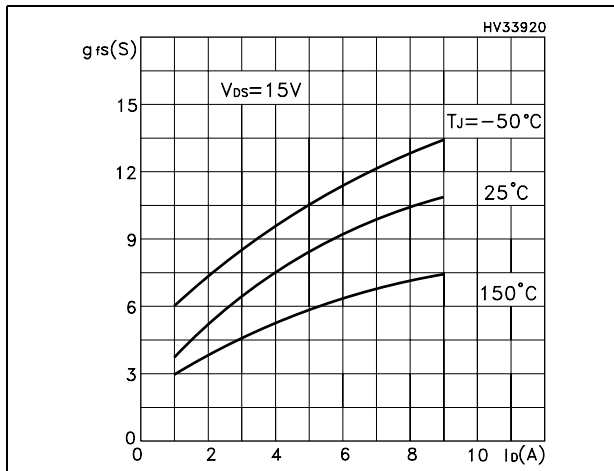


Figure 11. Static drain-source on resistance

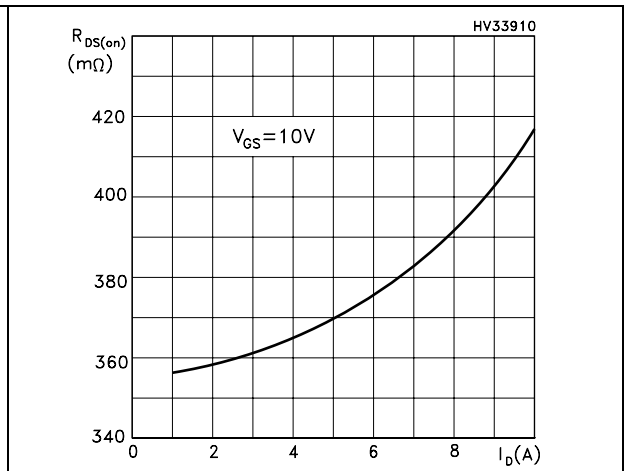


Figure 12. Gate charge vs gate-source voltage

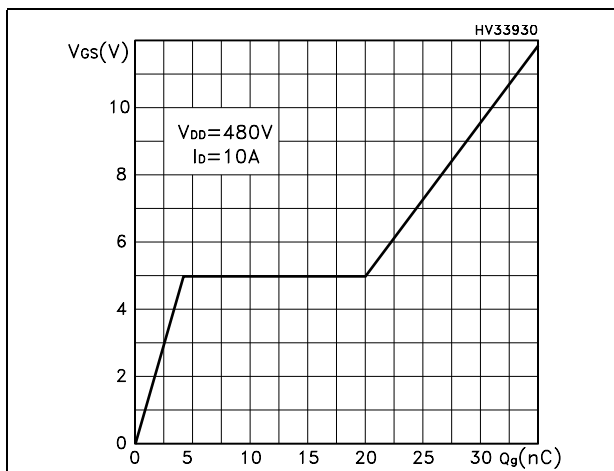


Figure 13. Capacitance variations

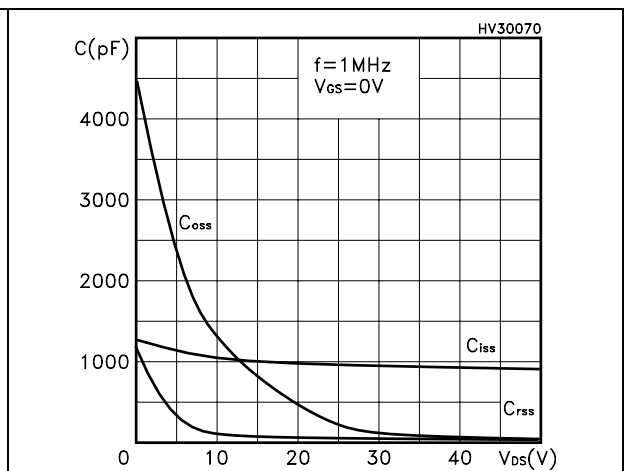


Figure 14. Normalized gate threshold voltage vs temperature

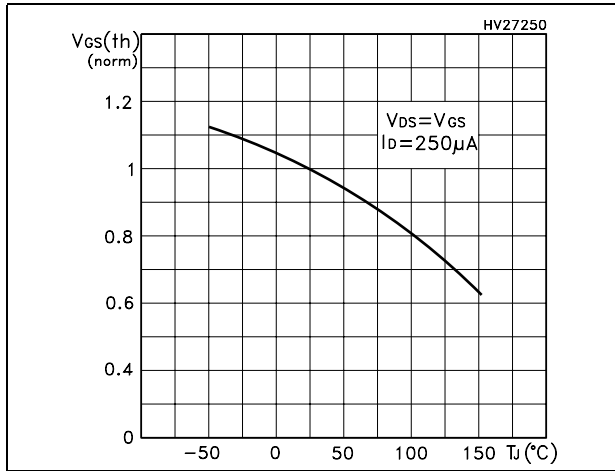


Figure 15. Normalized on resistance vs temperature

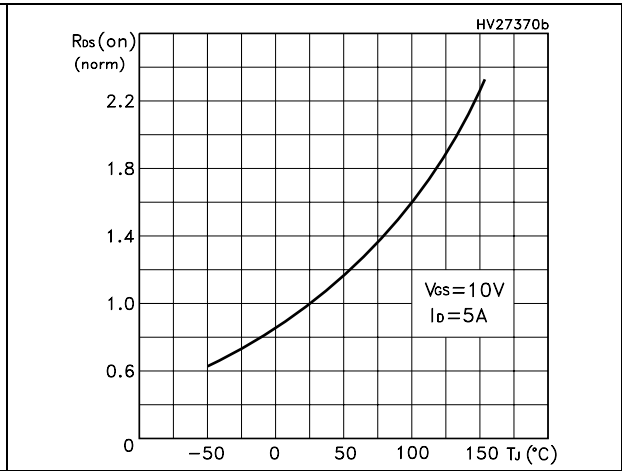


Figure 16. Source-drain diode forward characteristics

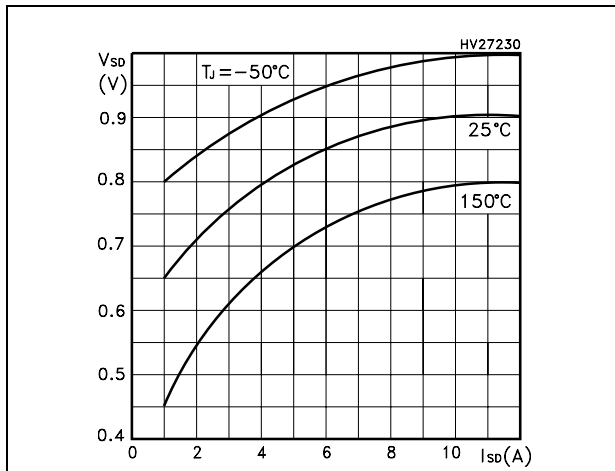
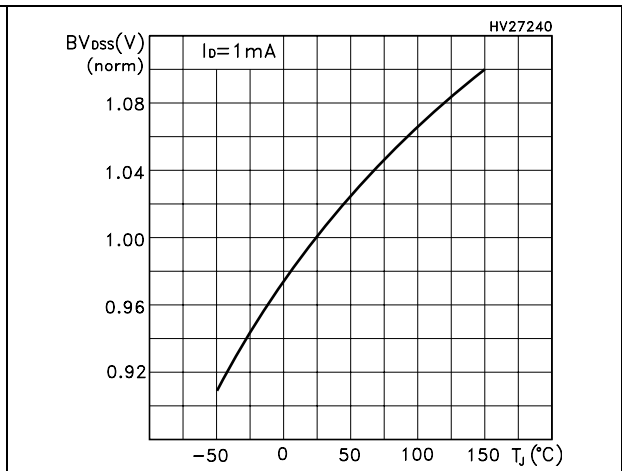


Figure 17. Normalized B_{VDSS} vs temperature



3 Test circuit

Figure 18. Switching times test circuit for resistive load



Figure 19. Gate charge test circuit



Figure 20. Test circuit for inductive load switching and diode recovery times



Figure 21. Unclamped inductive load test circuit



Figure 22. Unclamped inductive waveform



Figure 23. Switching time waveform

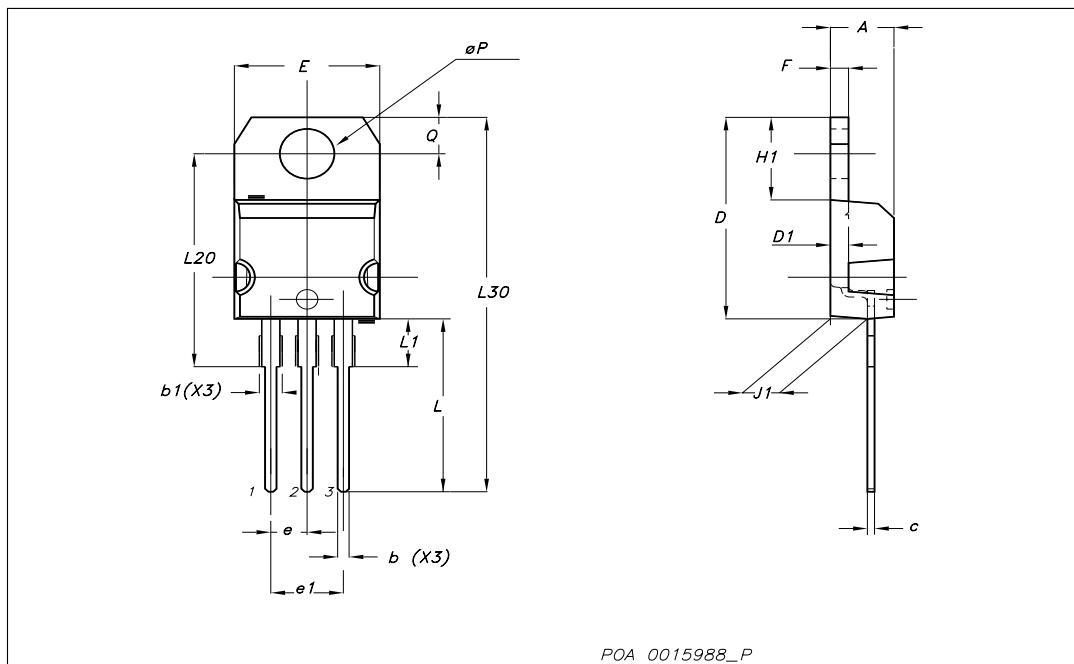


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

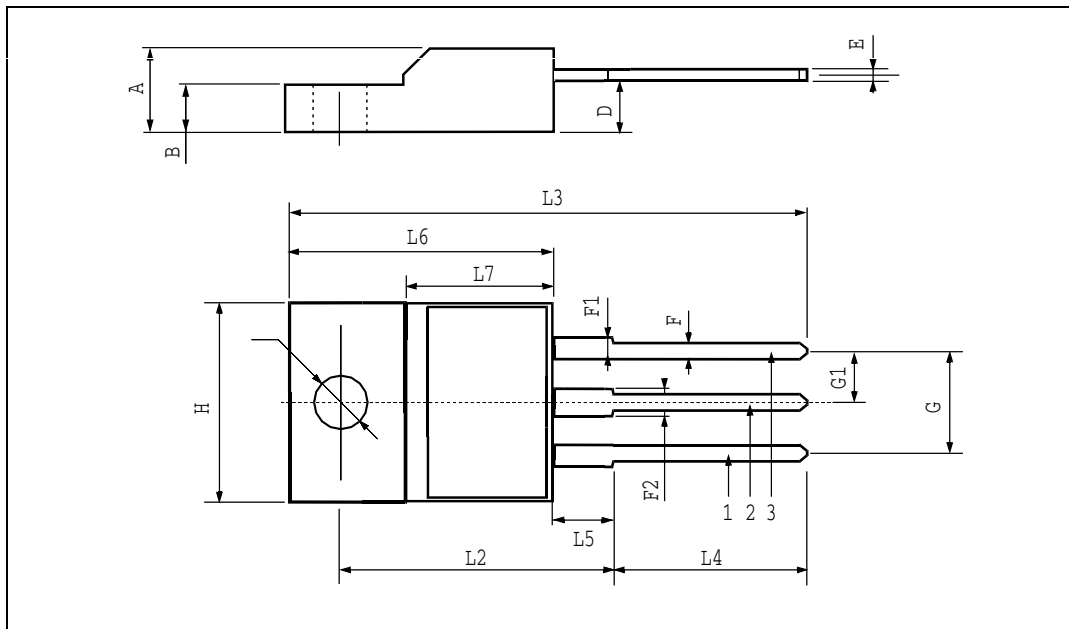
TO-220 mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.49		0.70	0.019		0.027
D	15.25		15.75	0.6		0.62
D1		1.27			0.050	
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.051
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
∅P	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



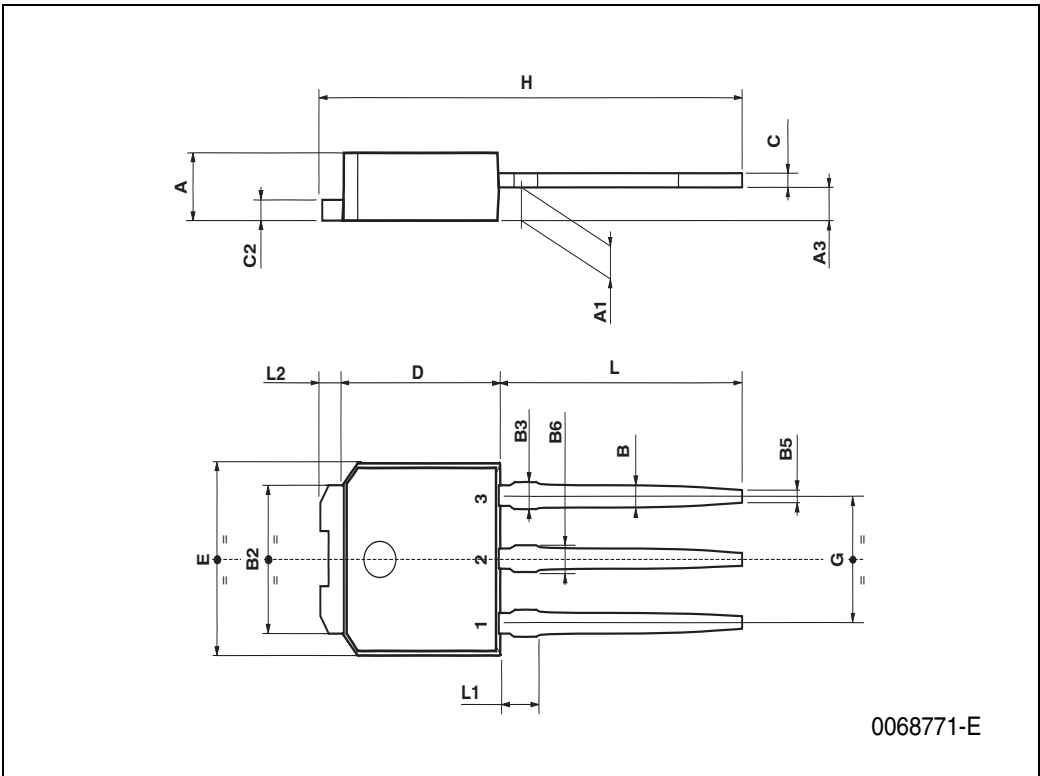
TO-220FP mechanical data

DIM.	mm.			inch		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	.0385		0.417
L5	2.9		3.6	0.114		0.141
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126



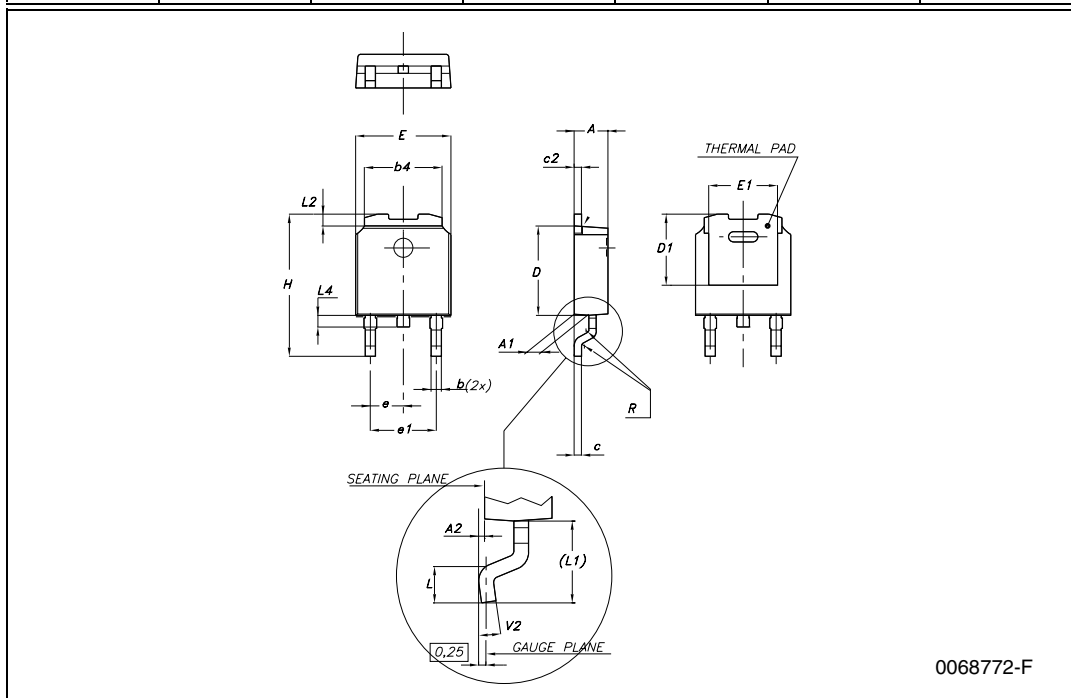
TO-251 (IPAK) mechanical data

DIM.	mm			inch		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.2		2.4	0.086		0.094
A1	0.9		1.1	0.035		0.043
A3	0.7		1.3	0.027		0.051
B	0.64		0.9	0.025		0.031
B2	5.2		5.4	0.204		0.212
B3			0.85			0.033
B5		0.3			0.012	
B6			0.95			0.037
C	0.45		0.6	0.017		0.023
C2	0.48		0.6	0.019		0.023
D	6		6.2	0.236		0.244
E	6.4		6.6	0.252		0.260
G	4.4		4.6	0.173		0.181
H	15.9		16.3	0.626		0.641
L	9		9.4	0.354		0.370
L1	0.8		1.2	0.031		0.047
L2		0.8	1		0.031	0.039



DPAK mechanical data

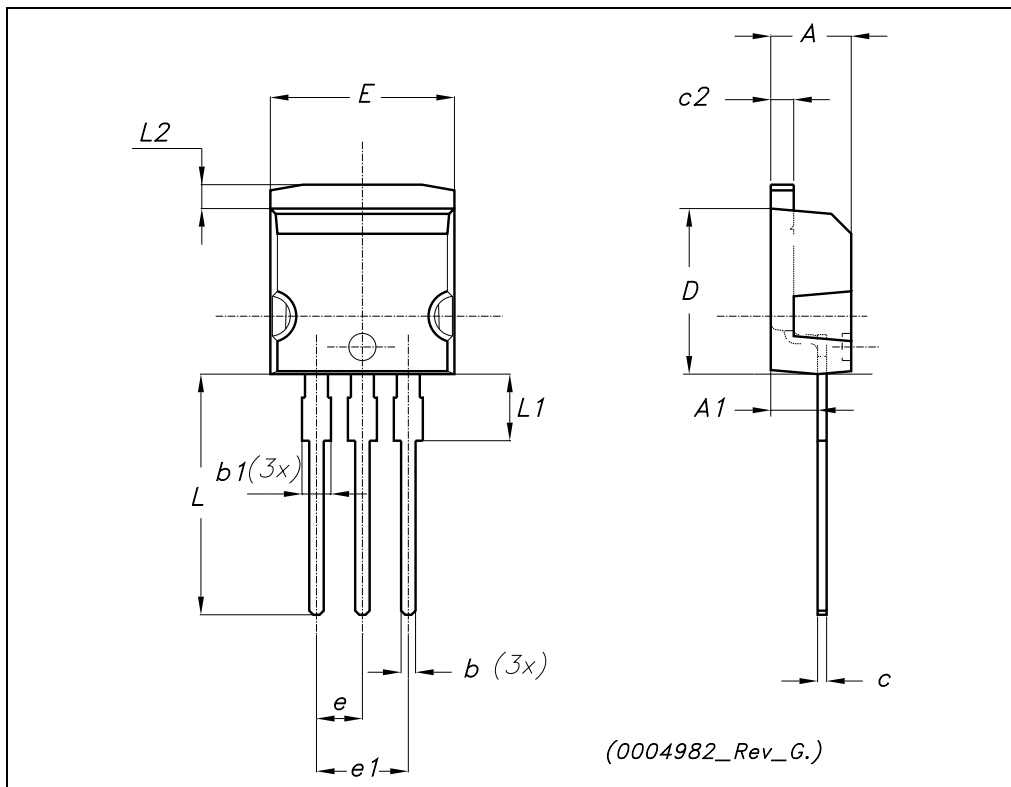
DIM.	mm.			inch		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.2		2.4	0.086		0.094
A1	0.9		1.1	0.035		0.043
A2	0.03		0.23	0.001		0.009
B	0.64		0.9	0.025		0.035
b4	5.2		5.4	0.204		0.212
C	0.45		0.6	0.017		0.023
C2	0.48		0.6	0.019		0.023
D	6		6.2	0.236		0.244
D1		5.1			0.200	
E	6.4		6.6	0.252		0.260
E1		4.7			0.185	
e		2.28			0.090	
e1	4.4		4.6	0.173		0.181
H	9.35		10.1	0.368		0.397
L	1			0.039		
(L1)		2.8			0.110	
L2		0.8			0.031	
L4	0.6		1	0.023		0.039
R		0.2			0.008	
V2	0°		8°	0°		8°



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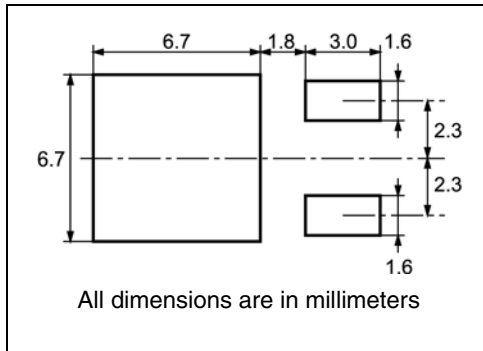
TO-262 (I²PAK) mechanical data

DIM.	mm.			inch		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
A1	2.40		2.72	0.094		0.107
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.49		0.70	0.019		0.027
c2	1.23		1.32	0.048		0.052
D	8.95		9.35	0.352		0.368
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
E	10		10.40	0.393		0.410
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L2	1.27		1.40	0.050		0.055



5 Packaging mechanical data

DPAK FOOTPRINT



TAPE AND REEL SHIPMENT

40 mm min. Access hole at slot location

Full radius

Tape slot in core for tape start 2.5mm min. width

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0.795	
G	16.4	18.4	0.645	0.724
N	50		1.968	
T		22.4		0.881

BASE QTY	BULK QTY
2500	2500

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	6.8	7	0.267	0.275
B0	10.4	10.6	0.409	0.417
B1		12.1		0.476
D	1.5	1.6	0.059	0.063
D1	1.5		0.059	
E	1.65	1.85	0.065	0.073
F	7.4	7.6	0.291	0.299
K0	2.55	2.75	0.100	0.108
P0	3.9	4.1	0.153	0.161
P1	7.9	8.1	0.311	0.319
P2	1.9	2.1	0.075	0.082
R	40		1.574	
W	15.7	16.3	0.618	0.641

TOP COVER TAPE

10 pitches cumulative tolerance on tape +/- 0.2 mm

Center line of cavity

User Direction of Feed

FEED DIRECTION

Bending radius R min.

6 Revision history

Table 9. Document revision history

Date	Revision	Changes
03-Aug-2006	1	First release
14-Nov-2006	2	Complete version
02-Oct-2007	3	Figure 8.: Output characteristics has been updated. Added new package (I ² PAK)

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